

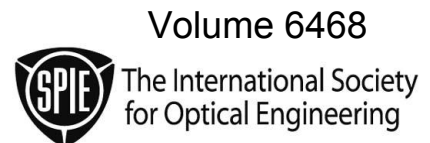
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**Marek Osiński
Fritz Henneberger
Yasuhiko Arakawa**
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